

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of	)	ATOMIC LAYER DEPOSITION
	)	METHOD AND SEMICONDUCTOR
Hwang et al.	)	DEVICE FABRICATING
	)	APPARATUS HAVING ROTATABLE
Application No.	)	GAS INJECTORS
	)	Group Art Unit:
Filing Date:	)	Examiner:

Commissioner for Patents  
P.O. Box 1450  
Mail Stop: Divisional Patent Application  
Alexandria, VA 22313-1450

**AMENDMENTS****AMENDMENT TO THE CLAIMS:**

Please cancel claims 4-14 which were allowed in the parent application.

Please prosecute claims 1-3 in this application.

**LISTING OF CLAIMS:**

1. (previously presented) An atomic layer deposition method comprising:  
respectively loading a plurality of substrates into a plurality of reaction cells, the plurality of reaction cells being disposed in a reaction chamber; and  
alternately and repeatedly applying various vapor substances onto each substrate such that a thin film is formed on each substrate, wherein a plurality of vapor injection pipes each injecting one of the vapor substances periodically scans over each substrate to apply the various vapor substances alternately and repeatedly onto each substrate.
2. (previously presented) The method of claim 1, wherein each substrate is heated using a heater disposed in the reaction chamber.
3. (previously presented) The method of claim 1, wherein RF power is applied to the vapor injection pipes such that plasma is generated in the reaction chamber.

4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (canceled)
11. (canceled)
12. (canceled)
13. (canceled)
14. (canceled)